BLP8G27-5

Power LDMOS transistor

Rev. 2 — 1 October 2015

AMPLEON

Product data sheet

1. Product profile

1.1 General description

5 W plastic LDMOS power transistor for base station applications at frequencies from 700 MHz to 2700 MHz.

Table 1. Application performance (multiple frequencies)

Typical RF performance at T_{case} = 25 °C; I_{Dq} = 55 mA; in a class-AB application circuit.

Test signal	f	I _{Dq}	V _{DS}	P _{L(AV)}	G _p	η_D	ACPR _{5M}
	(MHz)	(mA)	(V)	(dBm)	(dB)	(%)	(dBc)
2-carrier W-CDMA	2700	55	28	28.8	19	19	-50

^[1] Test signal: 2-carrier W-CDMA; test model 1; 10 MHz carrier spacing (mode 101); PAR = 8.3 dB at 0.01% probability on CCDF (46 % clipping).

1.2 Features and benefits

- High efficiency
- Excellent ruggedness
- Designed for broadband operation
- Excellent thermal stability
- High power gain
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

- CDMA
- W-CDMA
- GSM EDGE
- MC-GSM
- LTE
- WiMAX

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2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol [1]
1, 2, 5, 6, 7, 8, 9, 10, 11, 12, 15, 16	n.c.	16 9	13, 14
3, 4	gate		
13, 14	drain		3, 4 — — exposed
exposed die-pad	source [2]	1 8	die-pad
		Transparent top view	aaa-011340

- [1] To be used in single ended applications only.
- [2] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package	Package		
	Name	Description	Version	
BLP8G27-5		plastic thermal enhanced very thin small outline package; no leads;16 terminals; body 4 \times 6 \times 0.85 mm	SOT1371-1	

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-0.5	+13	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	225	°C

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-c)}	thermal resistance from junction to case	T_{case} = 80 °C; P_L = 1 W	6.4	K/W

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6. Characteristics

Table 6. DC characteristics

 T_i = 25 °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 0.09 \text{ mA}$	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS} = 10 \text{ V}; I_D = 9 \text{ mA}$	1.5	1.9	2.3	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 28 V	-1.4	-	+1.4	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 V$	-	1.6	-	Α
I _{GSS}	gate leakage current	V _{GS} = 11 V; V _{DS} = 0 V	-	-	140	nA
9 _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_{D} = 9 \text{ mA}$	-	80	-	mS
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}; I_D = 315 \text{ mA}$	-	2	-	Ω

Table 7. RF characteristics

A derivative functional RF test is performed in production. The performance as mentioned below is verified by design and characterization in an NXP class-AB application board.

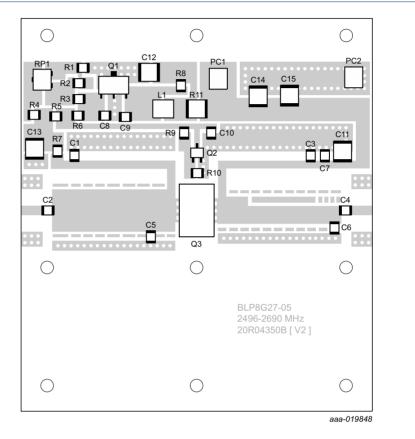
Test signal: pulsed CW; δ = 10%; t_p = 100 μ s; V_{DS} = 28 V; I_{Dq} = 55 mA; T_{case} = 25 °C; f = 2140 MHz

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	$P_{L(AV)} = 0.75 W$	17	18	-	dB
η_{D}	drain efficiency	P _{L(AV)} = 0.75 W	15	17	-	%
P _{L(1dB)}	output power at 1 dB gain compression		5	-	-	W

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7. Application information

7.1 Application circuit



Printed-Circuit Board (PCB): Rogers RO4350B; ϵ_{r} = 3.5; thickness = 0.508 mm; thickness copper plating = 35 μ m.

See Table 8 for list of components.

Fig 1. Component layout

Table 8. List of componentsSee Figure 1 for component layout.

Component	Description	Value	Remarks
C1, C2, C3, C4	multilayer ceramic chip capacitor	12 pF	ATC 100A
C5	multilayer ceramic chip capacitor	3 pF	ATC 100A
C6	multilayer ceramic chip capacitor	1.9 pF	ATC 100A
C7, C8, C9, C10	multilayer ceramic chip capacitor	100 nF, 50 V	Murata: GRM21BR71H104KA01L
C11, C12, C13	multilayer ceramic chip capacitor	4.7 μF, 50 V	Murata: GRM32ER71H475KA88L
C14, C15	multilayer ceramic chip capacitor	10 μF	AVX
RP1	potentiometer	10 turns	
R1	chip resistor	75 Ω	SMD 0805

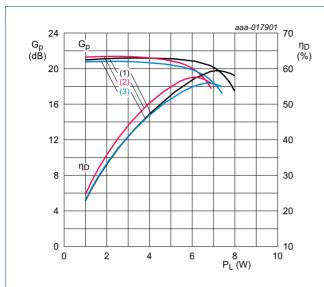
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Table 8. List of components ...continued See Figure 1 for component layout.

Component	Description	Value	Remarks
R2, R3	chip resistor	430 Ω	SMD 0805
R4	chip resistor	2 kΩ	SMD 0805
R5	chip resistor	11 kΩ	SMD 0805
R6	chip resistor	1.1 kΩ	SMD 0805
R7	chip resistor	2.0 kΩ	SMD 0805
R8	chip resistor	9.1 Ω	SMD 0805
R9	chip resistor	5.1 Ω	SMD 0805
R10	chip resistor	910 Ω	SMD 0805
R11	chip resistor	500 Ω, 1/4 W	leaded
L1	ferrite bead	1 μF, 50 V	Murata: GRM31MR71H105KA88L
Q1	surface-mounted package	-	SOT89
Q2	transistor	-	PMBT2222A
Q3	transistor	-	BLP8G27-5
PC1	power connector	-	positive supply
PC2	power connector	-	negative supply

7.2 Graphical data

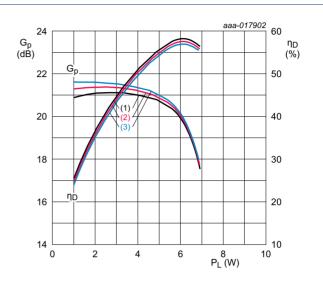
7.2.1 Pulsed CW



$$V_{DS}$$
 = 28 V; I_{Dq} = 55 mA; T_{case} = 25 °C; δ = 10 %; t_{D} = 100 μs .

- (1) f = 2110 MHz
- (2) f = 2140 MHz
- (3) f = 2170 MHz

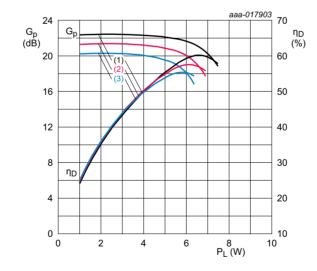
Fig 2. Power gain and drain efficiency as function of output power; typical values



$$V_{DS}$$
 = 28 V; T_{case} = 25 °C; f = 2140 MHz; δ = 10 %; t_{p} = 100 μ s.

- (1) $I_{Dq} = 45 \text{ mA}$
- (2) $I_{Dq} = 55 \text{ mA}$
- (3) $I_{Dq} = 65 \text{ mA}$

Fig 3. Power gain and drain efficiency as function of output power; typical values

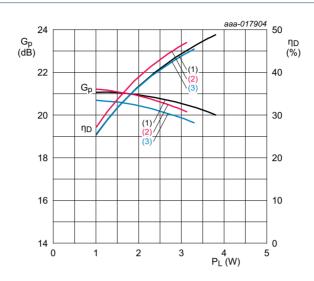


$$V_{DS}$$
 = 28 V; I_{Dq} = 55 mA; f = 2140 MHz; δ = 10 %; t_p = 100 μ s.

- (1) $T_{case} = -37 \, ^{\circ}C$
- (2) $T_{case} = +25 \, ^{\circ}C$
- (3) $T_{case} = +85 \, ^{\circ}C$

Fig 4. Power gain and drain efficiency as function of output power; typical values

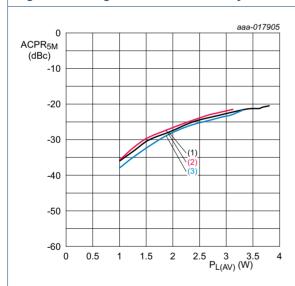
7.2.2 2-Carrier W-CDMA



V_{DS} = 28 V; I_{Dq} = 55 mA; T_{case} = 25 °C; carrier spacing = 5 MHz; 46 % clipping; PAR = 8.4 dB at 0.01 % probability on CCDF.

- (1) f = 2110 MHz
- (2) f = 2140 MHz
- (3) f = 2170 MHz

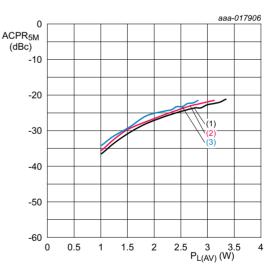
Fig 5. Power gain and drain efficiency as function of output power; typical values



 V_{DS} = 28 V; I_{Dq} = 55 mA; T_{case} = 25 °C; carrier spacing = 5 MHz; 46 % clipping; PAR = 8.4 dB at 0.01 % probability on CCDF.

- (1) f = 2110 MHz
- (2) f = 2140 MHz
- (3) f = 2170 MHz

Fig 6. Adjacent channel power ratio (5 MHz) as a function of average output power; typical values



 V_{DS} = 28 V; I_{Dq} = 55 mA; f = 2140 MHz; carrier spacing = 5 MHz; 46 % clipping; PAR = 8.4 dB at 0.01 % probability on CCDF.

- (1) $T_{case} = -37 \, ^{\circ}C$
- (2) $T_{case} = +25 \, ^{\circ}C$
- (3) $T_{case} = +85 \, ^{\circ}C$

Fig 7. Adjacent channel power ratio (5 MHz) as a function of average output power; typical values

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8. Test information

8.1 Ruggedness in class-AB operation

The BLP8G27-5 is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 28 V; I_{Dq} = 55 mA; P_L = 1 W; frequency from 700 MHz to 2700 MHz.

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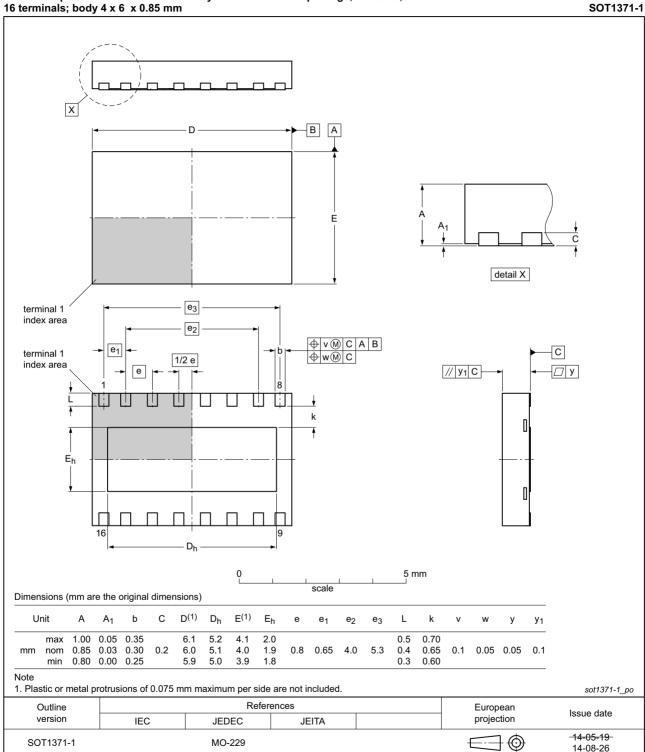
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Package outline

HVSON16: plastic thermal enhanced very thin small outline package; no leads;

SOT1371-1



Package outline SOT1371-1 (HVSON16) Fig 8.

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10. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

11. Abbreviations

Table 9. Abbreviations

Acronym	Description	
CCDF	Complementary Cumulative Distribution Function	
CDMA	Code Division Multiple Access	
CW	Continuous Wave	
EDGE	Enhanced Data rates for GSM Evolution	
ESD	ElectroStatic Discharge	
GSM	Global System for Mobile Communication	
LDMOS	Laterally Diffused Metal-Oxide Semiconductor	
LTE	Long Term Evolution	
MC-GSM	Multi Carrier GSM	
PAR	Peak-to-Average Ratio	
SMD	Surface Mounted Device	
VSWR	Voltage Standing-Wave Ratio	
W-CDMA	Wideband Code Division Multiple Access	
WiMAX	Worldwide Interoperability for Microwave Access	

12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BLP8G27-5 v.2	20151001	Product data sheet	-	BLP8G27-5 v.1	
Modifications:	The format of this document has been redesigned to comply with the new identity guidelines of Ampleon				
	Legal texts have been adapted to the new company name where appropriate				
BLP8G27-5 v.1	20150915	Product data sheet	-	-	

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13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
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